

## 具有三态输出的 SN74LVC1G126-Q1 单路总线缓冲门

### 1 特性

- 符合汽车应用要求
- 支持 5V  $V_{CC}$  运行
- 输入电压高达 5.5V
- 支持向下转换到  $V_{CC}$
- 低功耗， $I_{CC}$  最大值为 10  $\mu$ A
- 电压为 3.3V 时，输出驱动为  $\pm 24$ mA
- $I_{off}$  支持带电插入、局部断电模式和后驱动保护
- 闩锁性能超过 100mA，符合 JESD 78 II 类规范的要求

### 2 应用

- 线缆调制解调器终端系统
- 高速数据采集和生成
- 电机控制：高电压
- 电力线通信调制解调器
- SSD：内部或外部
- 视频广播和基础设施：可扩展平台
- 视频广播：基于 IP 的多格式转码器
- 视频通信系统

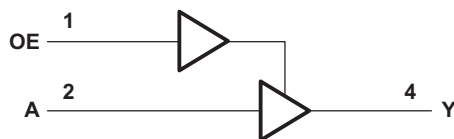
### 3 说明

SN74LVC1G126-Q1 器件是一款具有三态输出的单线驱动器。当输出使能输入为低电平时，输出被禁用。

#### 器件信息

器件型号	封装 (引脚) <sup>(1)</sup>	封装尺寸
1P1G126QDBVRQ1	SOT-23 (5)	2.90mm × 1.60mm
1P1G126QDRYRQ1	SON (6)	1.00mm × 1.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



简化版原理图



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## 4 Revision History

<b>Changes from Revision C (April 2019) to Revision D (August 2020)</b>	<b>Page</b>
• 更正了“特性”列表中的值。.....	1
• 更新了整个文档中的表格、图和交叉参考的编号格式.....	1
• 更新了说明和器件信息表.....	1
• Deleted incorrect history tags from revision C: Changed 1.65-V to 3.6-V VCC to 1.65-V to 5-V VCC operation and Changed MAX operating temperature to 125°C in Recommended Operating Conditions table.....	2
• Changed ESD ratings table to automotive format.....	4
• Corrected I <sub>OH</sub> and I <sub>OL</sub> MAX values in <i>Recommended Operating Conditions</i> table.....	5
• Corrected <i>Electrical Characteristics</i> table.....	6
• Removed <i>Switching Characteristics, CL = 15 pF</i> and <i>Switching Characteristics, -40°C to 85°C</i> tables.....	7
• Corrected MAX <i>Switching Characteristics</i> values.....	7
• Removed unneeded columns in <i>Operating Characteristics</i> table.....	7
• Removed first image and unused rows in table in <i>Parameter Measurement Information</i> section.....	8
• Updated <i>Feature Description</i> section.....	9
• Fixed cross references in <i>Detailed Design Procedure</i> section.....	11
<hr/>	
<b>Changes from Revision B (April 2008) to Revision C (April 2019)</b>	<b>Page</b>
• 将文档更新为新的 TI 数据表格式，删除了“订购信息”表，并添加了应用列表和器件信息表.....	1
• Added DRY package.....	3
• Added ESD ratings table.....	4
• Added <b>Thermal Information</b> table.....	5
• Added <i>Feature Description</i> section.....	9
• Added <i>Device Functional Modes</i> section.....	10
• Added <i>Application and Implementation</i> section.....	11
• Added <i>Power Supply Recommendations</i> and <i>Layout</i> sections.....	12
• Added <i>Device and Documentation Support</i> section and <i>Mechanical, Packaging, and Orderable Information</i> section.....	13

## 5 Pin Configuration and Functions

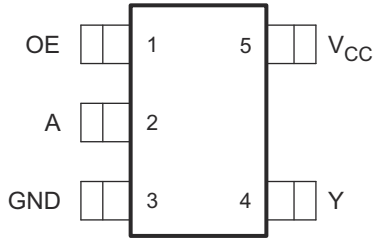
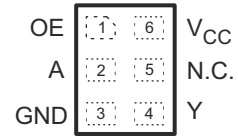


图 5-1. DBV Package 5-Pin SOT-23 Top View



N.C. is no connection

See all mechanical drawings at the end of this data sheet for package dimensions.

图 5-2. DRY Package 6-Pin SON Transparent Top View

### Pin Functions

NAME	PIN		TYPE	DESCRIPTION
	DBV (SOT-23)	DRY (SON)		
A	2	2	I	A Input
GND	3	3	—	Ground Pin
NC	—	5	—	No connection
OE	1	1	I	OE Enable/Input
V <sub>CC</sub>	5	6	—	Power Pin
Y	4	4	O	Y Output

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range	- 0.5	6.5	V
V <sub>I</sub>	Input voltage range <sup>(2)</sup>	- 0.5	6.5	V
V <sub>O</sub>	Voltage range applied to any output in the high-impedance or power-off state <sup>(2)</sup>	- 0.5	6.5	V
V <sub>O</sub>	Voltage range applied to any output in the high or low state <sup>(2) (3)</sup>	- 0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0	- 50	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0	- 50	mA
I <sub>O</sub>	Continuous output current		±50	mA
	Continuous current through V <sub>CC</sub> or GND		±100	mA
T <sub>stg</sub>	Storage temperature range	- 65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The value of V<sub>CC</sub> is provided in the *Recommended Operating Conditions* table.

### 6.2 ESD Ratings

PARAMETER	DEFINITION	VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 <sup>(1)</sup>	V
		Charged device model (CDM), per AEC Q100-011	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT	
V <sub>CC</sub>	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>		V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		
		V <sub>CC</sub> = 3 V to 3.6 V	2		
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.7 × V <sub>CC</sub>		
V <sub>IL</sub>	Low-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V		0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	
		V <sub>CC</sub> = 3 V to 3.6 V		0.8	
		V <sub>CC</sub> = 4.5 V to 5.5 V		0.3 × V <sub>CC</sub>	
V <sub>I</sub>	Input voltage	0	5.5	V	
V <sub>O</sub>	Output voltage	0	V <sub>CC</sub>	V	
I <sub>OH</sub>	High-level output current	V <sub>CC</sub> = 1.65 V		- 4	mA
		V <sub>CC</sub> = 2.3 V		- 8	
		V <sub>CC</sub> = 3 V		- 16	
		V <sub>CC</sub> = 4.5 V		- 24	
I <sub>OL</sub>	Low-level output current	V <sub>CC</sub> = 1.65 V		4	mA
		V <sub>CC</sub> = 2.3 V		8	
		V <sub>CC</sub> = 3 V		16	
		V <sub>CC</sub> = 4.5 V		24	
Δt/Δv	Input transition rise or fall rate	V <sub>CC</sub> = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V <sub>CC</sub> = 3.3 V ± 0.3 V		10	
		V <sub>CC</sub> = 5 V ± 0.5 V		5	
T <sub>A</sub>	Operating free-air temperature	- 40	125	°C	

(1) All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number [SCBA004](#).

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>	SN74LVC1G126-Q1		UNIT	
	DBV	DRY		
	5 PINS	6 PINS		
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	240.9	279.0	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	165.8	182.7	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	143.2	154.5	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	84.4	31.3	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	142.5	153.8	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	-	-	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

## 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V <sub>CC</sub>	MIN	TYP <sup>(1)</sup>	MAX	UNIT
V <sub>OH</sub>		I <sub>OH</sub> = - 100 μA	1.65 V to 5.5 V	V <sub>CC</sub> - 0.1			V
		I <sub>OH</sub> = - 4 mA	1.65 V	1.2			
		I <sub>OH</sub> = - 8 mA	2.3 V	1.9			
		I <sub>OH</sub> = - 16 mA	3 V	2.4			
		I <sub>OH</sub> = - 24 mA	3 V	2.3			
			4.5 V	3.8			
V <sub>OL</sub>		I <sub>OL</sub> = 100 μA	1.65 V to 5.5 V			0.1	V
		I <sub>OL</sub> = 4 mA	1.65 V			0.45	
		I <sub>OL</sub> = 8 mA	2.3 V			0.3	
		I <sub>OL</sub> = 16 mA	3 V			0.4	
		I <sub>OL</sub> = 24 mA	3 V			0.55	
			4.5 V			0.55	
I <sub>I</sub>	A or OE inputs	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			±5	μA
I <sub>off</sub>		V <sub>I</sub> or V <sub>O</sub> = 5.5 V	0			±10	μA
I <sub>OZ</sub>		V <sub>O</sub> = 0 to 5.5 V	3.6 V			10	μA
I <sub>CC</sub>		V <sub>I</sub> = 5.5 V or GND      I <sub>O</sub> = 0	1.65 V to 5.5 V			10	μA
Δ I <sub>CC</sub>		One input at V <sub>CC</sub> - 0.6 V, Other inputs at V <sub>CC</sub> or GND	3 V to 5.5 V			500	μA
C <sub>i</sub>		V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V		4		pF

(1) All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C.

## 6.6 Switching Characteristics

over recommended operating free-air temperature range,  $C_L = 50$  pF (unless otherwise noted) (see 图 7-1)

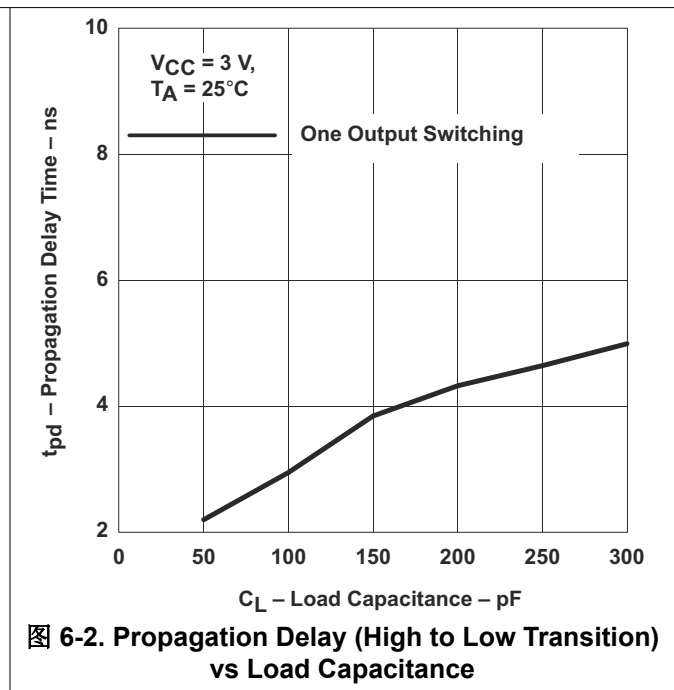
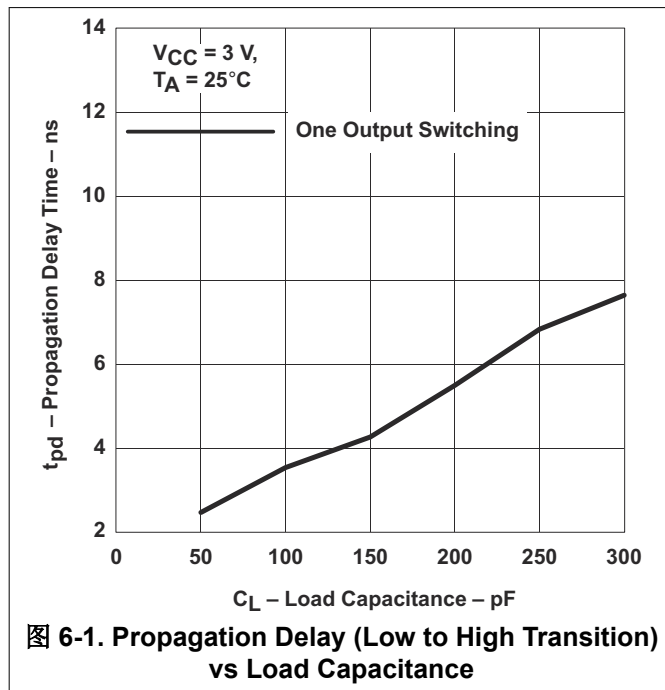
PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$		$V_{CC} = 5\text{ V} \pm 0.5\text{ V}$		UNIT
			MIN	MAX	MIN	MAX	
$t_{pd}$	A	Y	1	5.8	1	4.5	ns
$t_{en}$	OE	Y	1.2	5.8	1	5	ns
$t_{dis}$	OE	Y	1	6	1	4.2	ns

## 6.7 Operating Characteristics

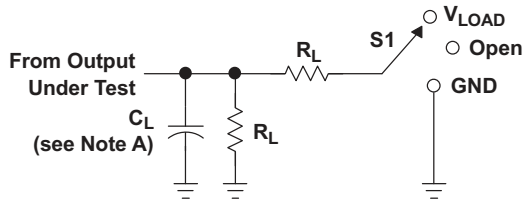
$T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	$V_{CC} = 3.3\text{ V}$	$V_{CC} = 5\text{ V}$	UNIT
			TYP	TYP	
$C_{pd}$	Power dissipation capacitance	Outputs enabled	19	21	pF
			Outputs disabled	3	

## 6.8 Typical Characteristics



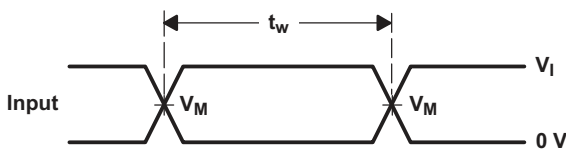
## 7 Parameter Measurement Information



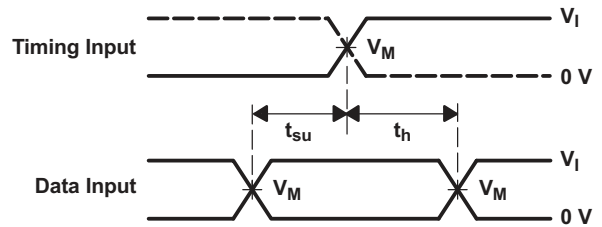
LOAD CIRCUIT

TEST	S1
$t_{PLH}/t_{PHL}$	Open
$t_{PLZ}/t_{PZL}$	$V_{LOAD}$
$t_{PHZ}/t_{PZH}$	GND

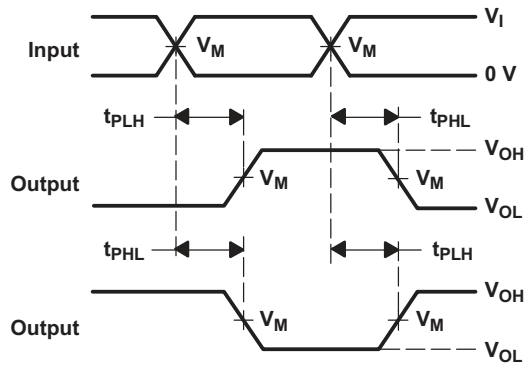
$V_{CC}$	INPUTS		$V_M$	$V_{LOAD}$	$C_L$	$R_L$	$V_{\Delta}$
	$V_I$	$t_r/t_f$					
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 $\Omega$	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	$V_{CC}$	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 $\Omega$	0.3 V



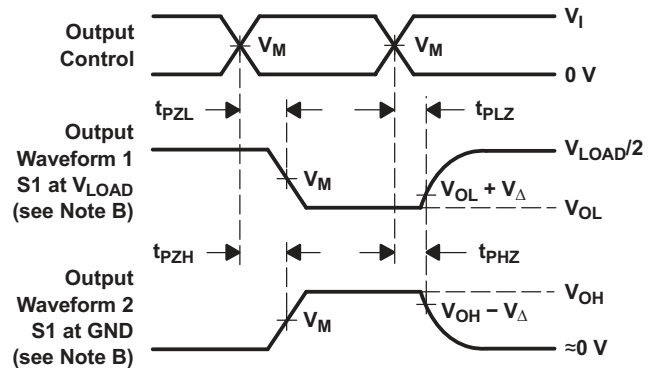
VOLTAGE WAVEFORMS PULSE DURATION



VOLTAGE WAVEFORMS SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

- NOTES: A.  $C_L$  includes probe and jig capacitance.  
 B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.  
 C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10\text{ MHz}$ ,  $Z_O = 50\ \Omega$ .  
 D. The outputs are measured one at a time, with one transition per measurement.  
 E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .  
 F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .  
 G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .  
 H. All parameters and waveforms are not applicable to all devices.

图 7-1. Load Circuit and Voltage Waveforms



## 8 Detailed Description

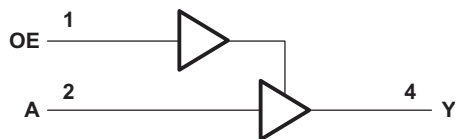
### 8.1 Overview

The SN74LVC1G126-Q1 device contains a dual buffer gate with output enable control and performs the Boolean function  $Y = A$ .

This device is fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pull-down resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

### 8.2 Functional Block Diagram



### 8.3 Feature Description

#### 8.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-State outputs. The three states that these outputs can be in are driving high, driving low, and high impedance. The term "balanced" indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance mode, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10 k $\Omega$  resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

#### 8.3.2 Partial Power Down ( $I_{off}$ )

This device includes circuitry to disable all outputs when the supply pin is held at 0 V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the  $I_{off}$  specification in the *Electrical Characteristics* table.

#### 8.3.3 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law ( $R = V \div I$ ).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in [Implications of Slow or Floating CMOS Inputs](#).

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at  $V_{CC}$  or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be

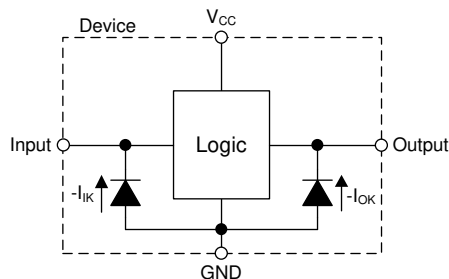
added to provide a valid input voltage during these times. The resistor value will depend on multiple factors, however a 10-kΩ resistor is recommended and will typically meet all requirements.

### 8.3.4 Clamp Diode Structure

The inputs and outputs to this device have negative clamping diodes only as depicted in [图 8-1](#).

**CAUTION**

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.



**图 8-1. Electrical Placement of Clamping Diodes for Each Input and Output**

## 8.4 Device Functional Modes

**表 8-1. Function Table**

INPUTS		OUTPUT Y
OE	A	
H	H	H
H	L	L
L	X	Z

## 9 Application and Implementation

### Note

以下应用部分的信息不属于 TI 组件规范，TI 不担保其准确性和完整性。客户应负责确定 TI 组件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

### 9.1 Application Information

The SN74LVC1G126-Q1 device is a high-drive CMOS device that can be used as an output enabled buffer with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V, making it ideal for driving multiple outputs and good for high speed applications up to 100 MHz. The inputs are 5.5-V tolerant allowing it to translate down to  $V_{CC}$ .

### 9.2 Typical Application

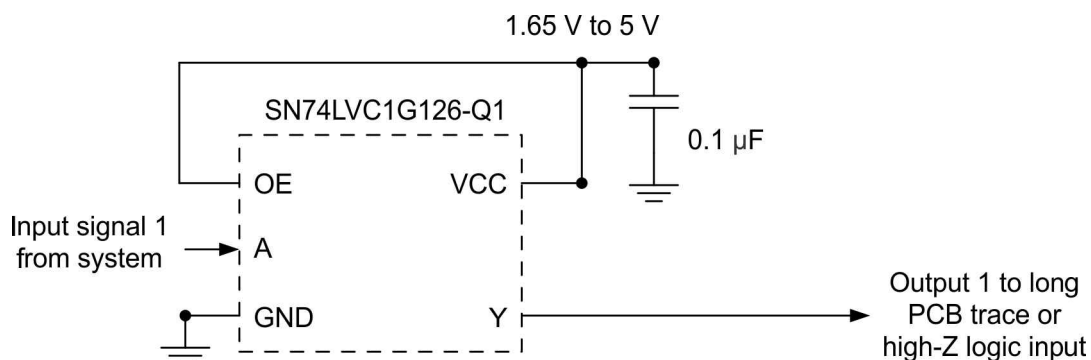


图 9-1. Application Schematic

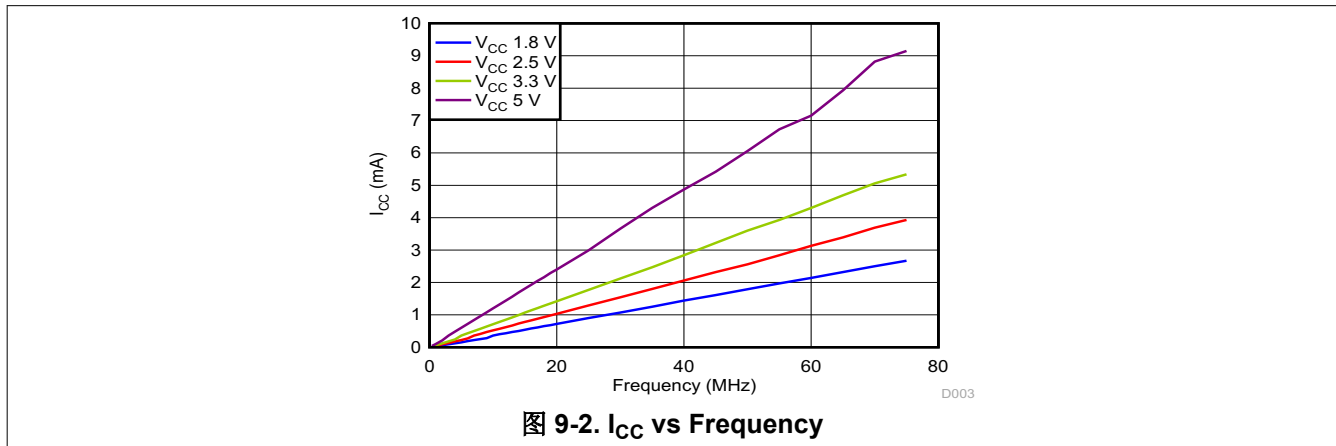
#### 9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. Outputs can be combined to produce higher drive but the high drive will also create faster edges into light loads, so routing and load conditions should be considered to prevent ringing.

#### 9.2.2 Detailed Design Procedure

1. Recommended Input Conditions:
  - For rise time and fall time specifications, see  $\Delta t / \Delta V$  in the [Recommended Operating Conditions](#) table.
  - For specified high and low levels, see  $V_{IH}$  and  $V_{IL}$  in the [Recommended Operating Conditions](#) table.
  - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid  $V_{CC}$ .
2. Recommend Output Conditions:
  - Load currents should not exceed 50 mA per output and 100 mA total for the part.

### 9.2.3 Application Curves



## 10 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the [Recommended Operating Conditions](#) table.

Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- $\mu$ F capacitor is recommended. If there are multiple  $V_{CC}$  terminals, then 0.01- $\mu$ F or 0.022- $\mu$ F capacitors are recommended for each power terminal. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. Multiple bypass capacitors may be paralleled to reject different frequencies of noise. The bypass capacitor should be installed as close to the power terminal as possible for the best results.

## 11 Layout

### 11.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in [Recommended Operating Conditions](#) are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or  $V_{CC}$ , whichever makes more sense or is more convenient. It is acceptable to float outputs unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the outputs section of the part when asserted. This will not disable the input section of the I/Os so they also cannot float when disabled.

### 11.2 Layout Example

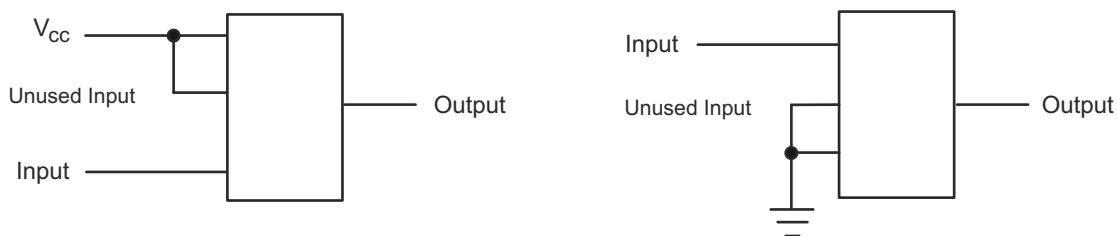


图 11-1. Layout Diagram

## 12 Device and Documentation Support

### 12.1 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](http://ti.com) 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

### 12.2 支持资源

[TI E2E™ 中文支持论坛](#) 是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [使用条款](#)。

### 12.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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### 12.4 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

### 12.5 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
1P1G126QDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C26O	<b>Samples</b>
1P1G126QDRYRQ1	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HN	<b>Samples</b>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
1P1G126QDBVRQ1	SOT-23	DBV	5	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
1P1G126QDRYRQ1	SON	DRY	6	5000	180.0	9.5	1.2	1.65	0.7	4.0	8.0	Q1



**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
1P1G126QDBVRQ1	SOT-23	DBV	5	3000	200.0	183.0	25.0
1P1G126QDRYRQ1	SON	DRY	6	5000	189.0	185.0	36.0

## GENERIC PACKAGE VIEW

**DRY 6**

**USON - 0.6 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.

4207181/G

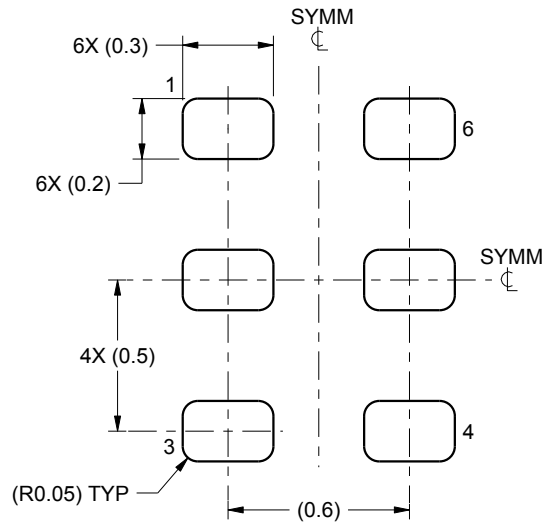


# EXAMPLE BOARD LAYOUT

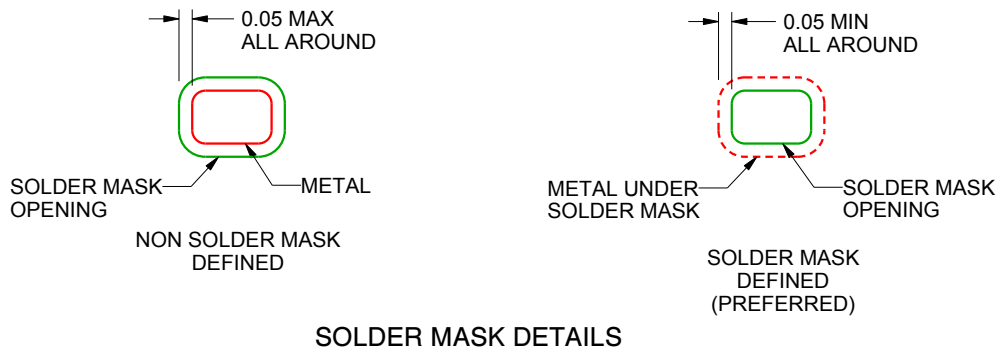
DRY0006B

USON - 0.55 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE  
1:1 RATIO WITH PKG SOLDER PADS  
SCALE:40X



4222207/B 02/2016

NOTES: (continued)

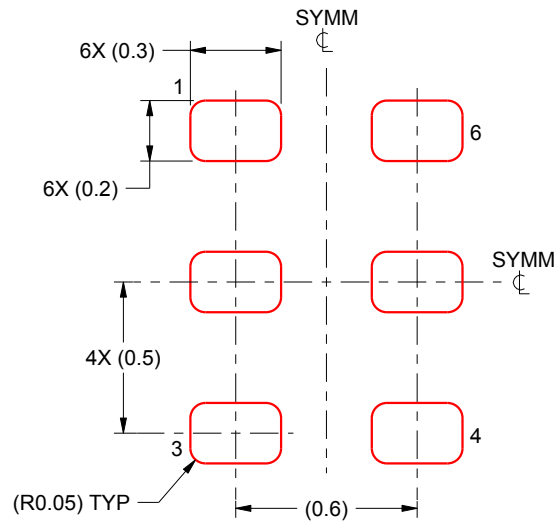
3. For more information, see QFN/SON PCB application report in literature No. SLUA271 ([www.ti.com/lit/sluea271](http://www.ti.com/lit/sluea271)).

# EXAMPLE STENCIL DESIGN

DRY0006B

USON - 0.55 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE  
BASED ON 0.075 - 0.1 mm THICK STENCIL  
SCALE:40X

4222207/B 02/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

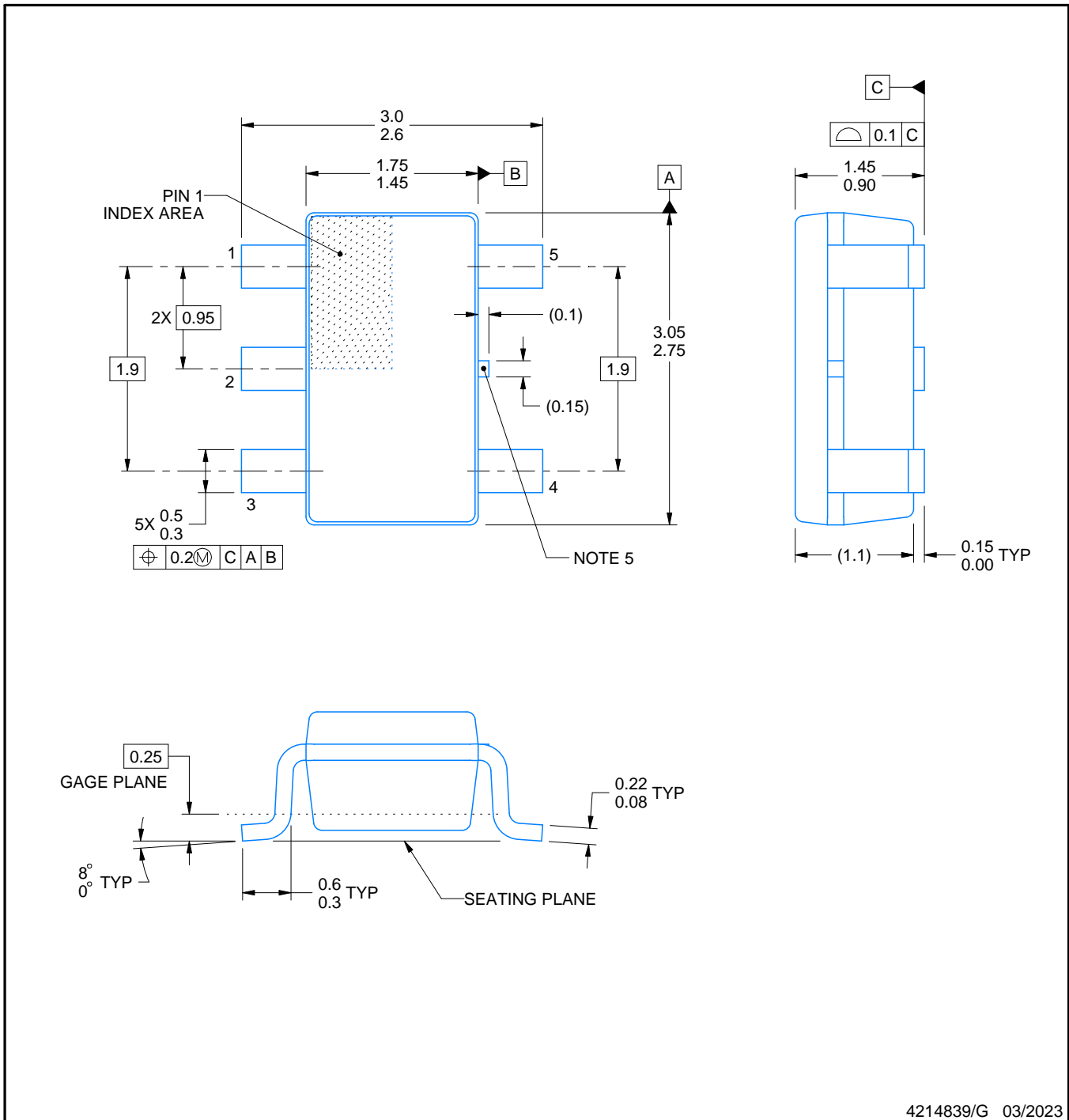
DBV0005A



# PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



4214839/G 03/2023

NOTES:

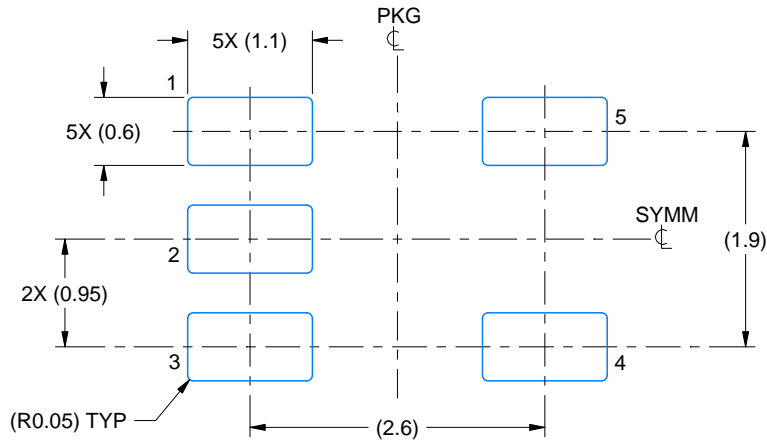
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.

# EXAMPLE BOARD LAYOUT

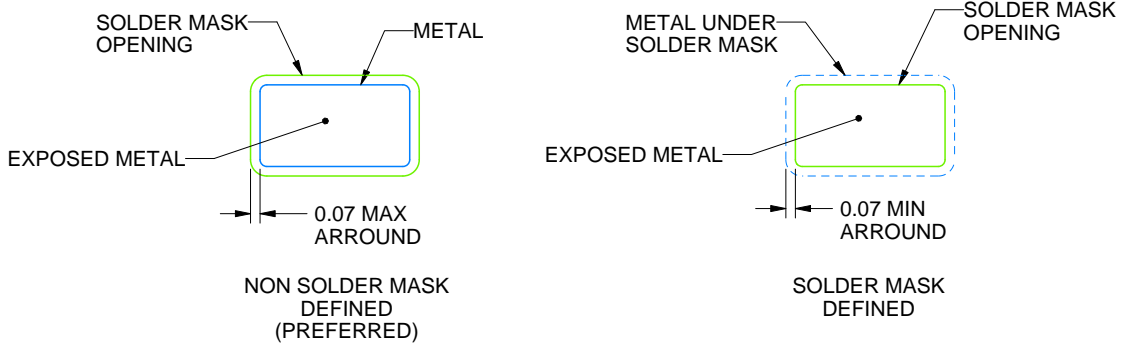
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:15X



SOLDER MASK DETAILS

4214839/G 03/2023

NOTES: (continued)

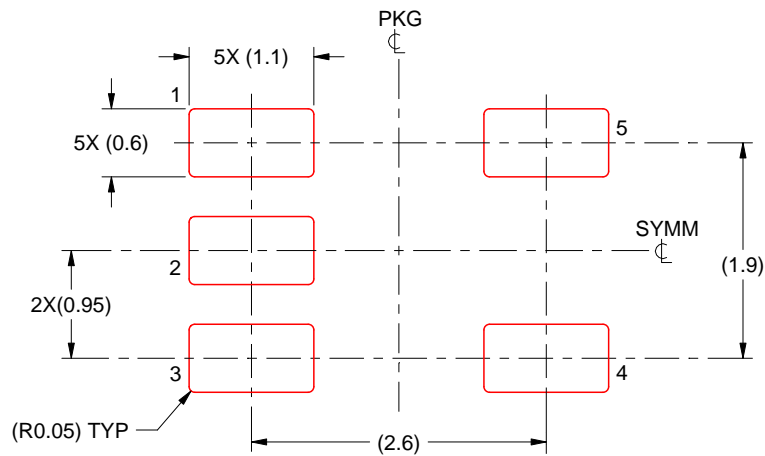
- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:15X

4214839/G 03/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



## 重要声明和免责声明

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